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(54) Title: METHODS FOR REMOVING AN OXIDE FILM FROM A SOI STRUCTURE AND METHODS FOR PREPARING A
SOI STRUCTURE

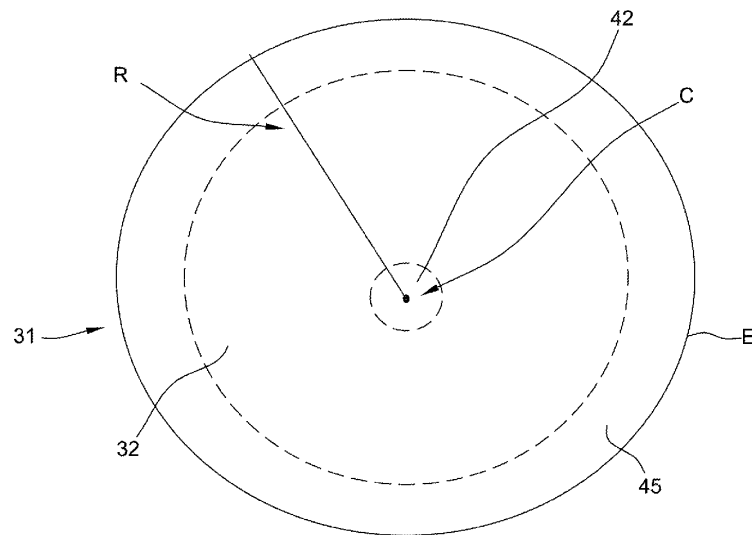


FIG. 7

(57) Abstract: Methods for removing an oxide film from a silicon-on-insulator structure are disclosed. The oxide may be stripped from a SOI structure before deposition of an epitaxial silicon thickening layer. The oxide film may be removed by dispensing an etching solution toward a center region of the SOI structure and dispensing an etching solution to an edge region of the structure.

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